Features

- **Low-voltage and Standard-voltage Operation**
  - **V_{CC} = 1.7V to 5.5V**
- **Internally Organized 256 x 8 (2K)**
- **Two-wire Serial Interface**
- **Schmitt Trigger, Filtered Inputs for Noise Suppression**
- **Bidirectional Data Transfer Protocol**
- **1 MHz (5V), 400 kHz (1.7V, 2.5V, 2.7V) Compatibility**
- **Write Protect Pin for Hardware Data Protection**
- **8-byte Page (2K) Write Modes**
- **Partial Page Writes Allowed**
- **Self-timed Write Cycle (5 ms max)**
- **High-reliability**
  - **Endurance: 1 Million Write Cycles**
  - **Data Retention: 100 Years**
- **Green (Pb/Halide-free/RoHS Compliant) Package Options**
- **Die Sales: Wafer Form and Tape and Reel**

Description

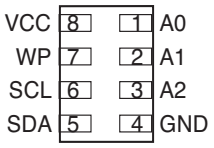
The AT24C02C provides 2048 bits of serial electrically erasable and programmable read-only memory (EEPROM) organized as 256 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The AT24C02C is available in space-saving 8-lead PDIP, 8-lead JEDEC SOIC, 8-lead UDFN, 5-lead SOT23, 8-lead TSSOP, and 8-ball VFBGA packages and is accessed via a Two-wire serial interface.

Table 0-1. Pin Configuration

Pin Name	Function
A0 - A2	Address Inputs
SDA	Serial Data
SCL	Serial Clock Input
WP	Write Protect
GND	Ground
VCC	Power Supply

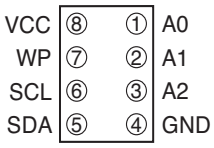
Note: For use of 5-lead SOT23, the software A2, A1, and A0 bits in the device address word must be set to zero to properly communicate.

8-lead UDFN



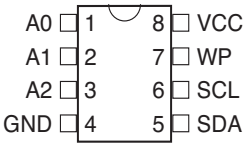
Bottom View

8-ball VFBGA

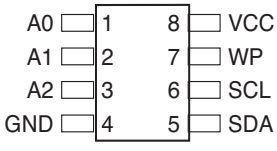


Bottom View

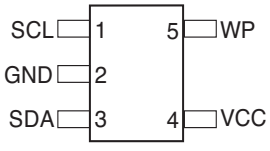
8-lead TSSOP



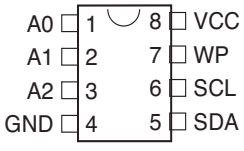
8-lead SOIC



5-lead SOT23



8-lead PDIP



Two-wire Serial EEPROM

2K (256 x 8)

AT24C02C Preliminary

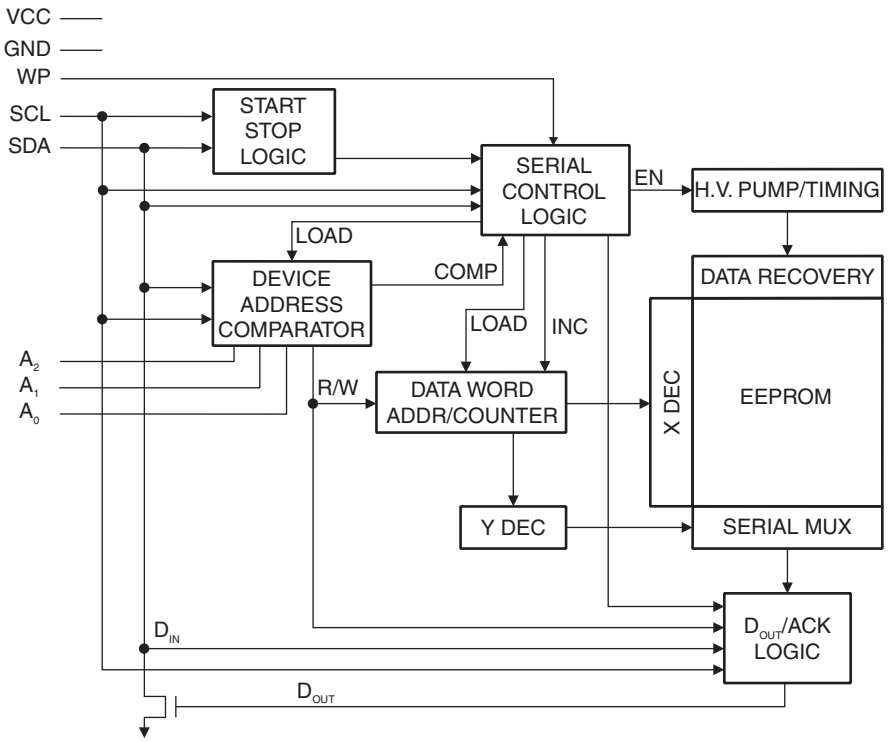
8700B–DEEPR–2/10

Absolute Maximum Ratings

Operating Temperature	–55°C to +125°C
Storage Temperature	–65°C to +150°C
Voltage on Any Pin with Respect to Ground	–1.0V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current	5.0 mA

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure 0-1. Block Diagram



1. Pin Description

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

SERIAL DATA (SDA): The SDA pin is bidirectional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

DEVICE/PAGE ADDRESSES (A2, A1, A0): The A2, A1 and A0 pins are device address inputs that are hard wired for the AT24C02C. As many as eight 2K devices may be addressed on a single bus system (device addressing is discussed in detail under the Device Addressing section).

WRITE PROTECT (WP): The AT24C02C has a write protect pin that provides hardware data protection. The write protect pin allows normal read/write operations when connected to ground

(GND). When the write protect pin is connected to V_{CC}, the write protection feature is enabled and operates as shown in Table 1-1.

Table 1-1. Write Protect

WP Pin Status	Part of the Array Protected
	24C02C
At V_{CC}	Full (2K) Array
At GND	Normal Read/Write Operations

2. Memory Organization

AT24C02C, 2K SERIAL EEPROM: Internally organized with 32 pages of 8 bytes each, the 2K requires an 8-bit data word address for random word addressing.

Table 2-1. Pin Capacitance[1]

Applicable over recommended operating range from T_A = 25°C, f = 1.0 MHz, V_{CC} = +1.7V to +5.5V

Symbol	Test Condition	Max	Units	Conditions
$C_{I/O}$	Input/Output Capacitance (SDA)	8	pF	$V_{I/O}$ = 0V
C_{IN}	Input Capacitance (A_0, A_1, A_2, SCL)	6	pF	V_{IN} = 0V

Note: 1. This parameter is characterized and is not 100% tested.

Table 2-2. DC Characteristics

Applicable over recommended operating range from: T_{AI} = –40°C to +85°C, V_{CC} = +1.7V to +5.5V (unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Units
V_{CC1}	Supply Voltage		1.7		5.5	V
V_{CC2}	Supply Voltage		2.5		5.5	V
V_{CC3}	Supply Voltage		2.7		5.5	V
V_{CC4}	Supply Voltage		4.5		5.5	V
I_{CC}	Supply Current V_{CC} = 5.0V	READ at 100 kHz		0.4	1.0	mA
I_{CC}	Supply Current V_{CC} = 5.0V	WRITE at 100 kHz		2.0	3.0	mA
I_{SB1}	Standby Current V_{CC} = 1.7V	V_{IN} = V_{CC} or V_{SS}		0.6	3.0	µA
I_{SB2}	Standby Current V_{CC} = 2.5V	V_{IN} = V_{CC} or V_{SS}		1.4	4.0	µA
I_{SB3}	Standby Current V_{CC} = 2.7V	V_{IN} = V_{CC} or V_{SS}		1.6	4.0	µA
I_{SB4}	Standby Current V_{CC} = 5.0V	V_{IN} = V_{CC} or V_{SS}		8.0	18.0	µA
I_{LI}	Input Leakage Current	V_{IN} = V_{CC} or V_{SS}		0.10	3.0	µA
I_{LO}	Output Leakage Current	V_{OUT} = V_{CC} or V_{SS}		0.05	3.0	µA
V_{IL}	Input Low Level[1]		–0.6		V_{CC} x 0.3	V
V_{IH}	Input High Level[1]		V_{CC} x 0.7		V_{CC} + 0.5	V
V_{OL2}	Output Low Level V_{CC} = 3.0V	I_{OL} = 2.1 mA			0.4	V
V_{OL1}	Output Low Level V_{CC} = 1.7V	I_{OL} = 0.15 mA			0.2	V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

Table 2-3. AC Characteristics

Applicable over recommended operating range from T_{AI} = –40°C to +85°C, V_{CC} = +1.7V to +5.5V, CL = 1 TTL Gate and 100 pF (unless otherwise noted)

Symbol	Parameter	1.7, 2.5, 2.7		5.0-volt		Units
		Min	Max	Min	Max	
f_{SCL}	Clock Frequency, SCL		400		1000	kHz
t_{LOW}	Clock Pulse Width Low	1.2		0.4		µs
t_{HIGH}	Clock Pulse Width High	0.6		0.4		µs
t_I	Noise Suppression Time		50		40	ns
t_{AA}	Clock Low to Data Out Valid	0.1	0.9	0.05	0.55	µs
t_{BUF}	Time the bus must be free before a new transmission can start	1.2		0.5		µs

Table 2-3. AC Characteristics

Applicable over recommended operating range from T_{AI} = –40°C to +85°C, V_{CC} = +1.7V to +5.5V, CL = 1 TTL Gate and 100 pF (unless otherwise noted)

Symbol	Parameter	1.7, 2.5, 2.7		5.0-volt		Units
		Min	Max	Min	Max	
$t_{HD.STA}$	Start Hold Time	0.6		0.25		µs
$t_{SU.STA}$	Start Setup Time	0.6		0.25		µs
$t_{HD.DAT}$	Data In Hold Time	0		0		µs
$t_{SU.DAT}$	Data In Setup Time	100		100		ns
t_R	Inputs Rise Time(1)		0.3		0.3	µs
t_F	Inputs Fall Time(1)		300		100	ns
$t_{SU.STO}$	Stop Setup Time	0.6		.25		µs
t_{DH}	Data Out Hold Time	50		50		ns
t_{WR}	Write Cycle Time		5		5	ms
Endurance(1)	5.0V, 25°C, Byte Mode	1 Million				Write Cycles

Note: 1. This parameter is ensured by characterization only.

3. Device Operation

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (see Figure 5-2 on page 8). Data changes during SCL high periods will indicate a start or stop condition as defined below.

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (see Figure 5-3 on page 8).

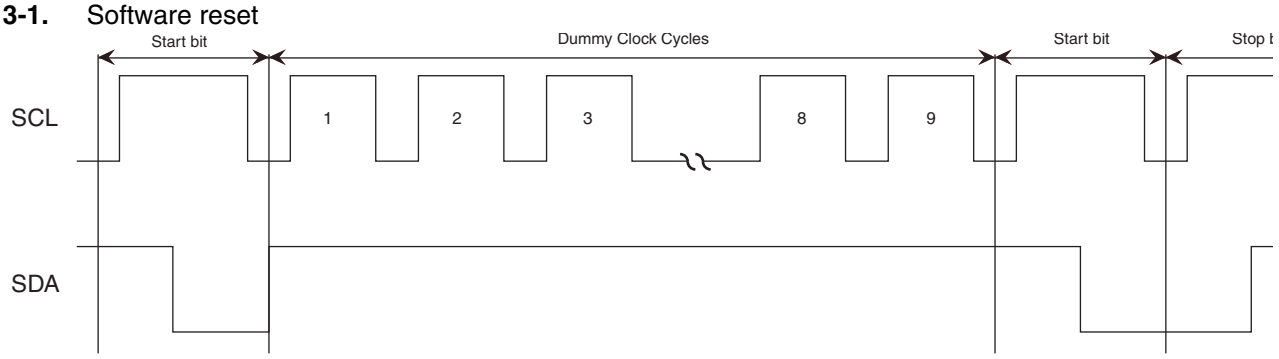
STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (see Figure 5-3 on page 8).

ACKNOWLEDGE: All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a zero to acknowledge that it has received each word. This happens during the ninth clock cycle.

STANDBY MODE: The AT24C02C features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the STOP bit and the completion of any internal operations.

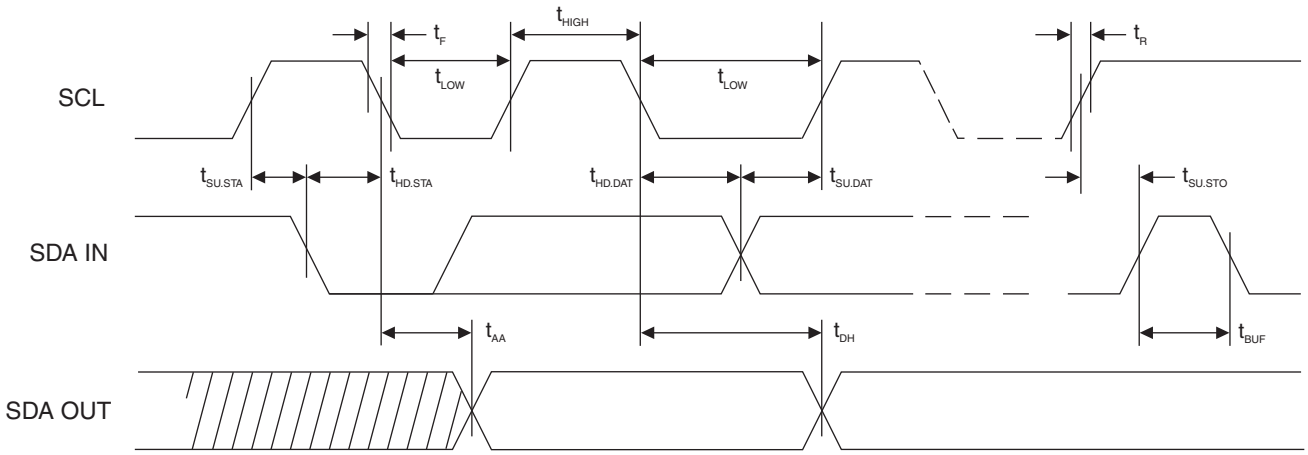
2-Wire Software Reset: After an interruption in protocol, power loss or system reset, any 2-wire part can be reset by following these steps: (a) Create a start bit condition, (b) clock 9 cycles, (c) create another start bit followed by stop bit condition as shown below. The device is ready for next communication after above steps have been completed.

Figure 3-1. Software reset



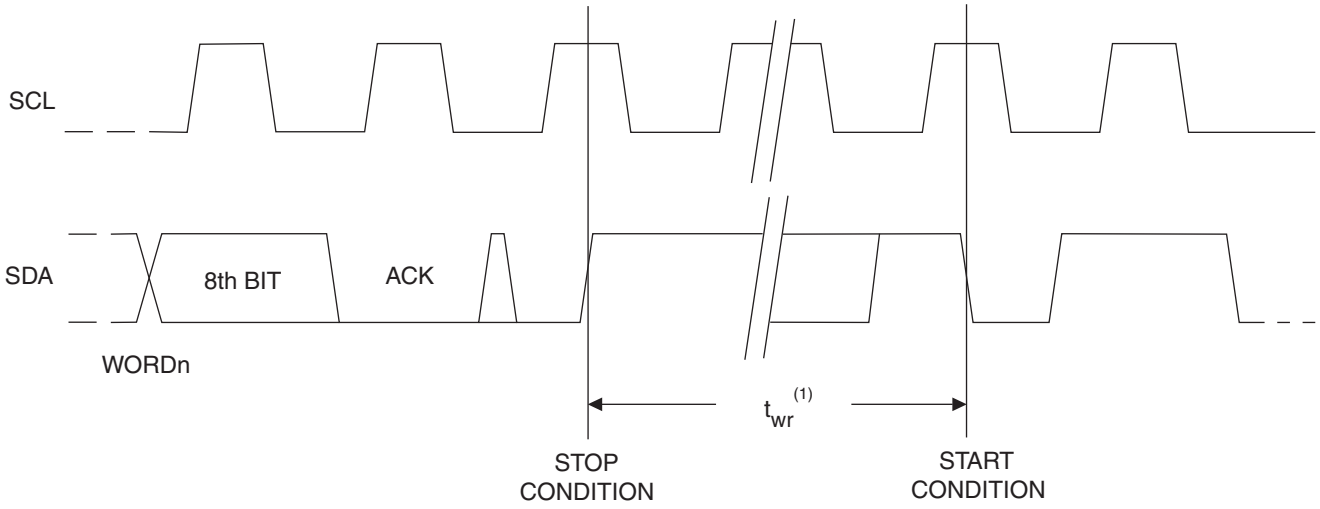
4. Bus Timing

Figure 4-1. SCL: Serial Clock, SDA: Serial Data I/O®



5. Write Cycle Timing

Figure 5-1. SCL: Serial Clock, SDA: Serial Data I/O



Note: 1. The write cycle time t_{WR} is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

Figure 5-2. Data Validity

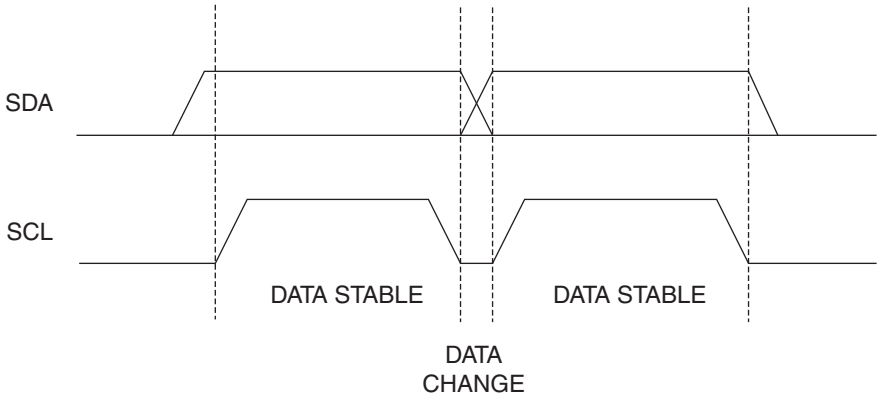


Figure 5-3. Start and Stop Definition

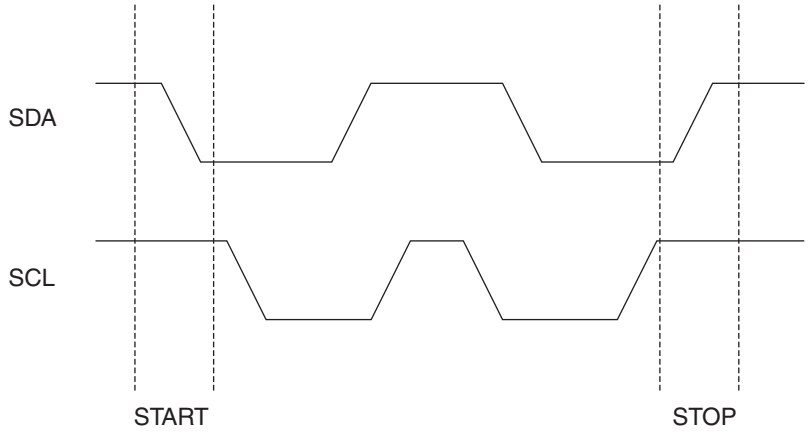
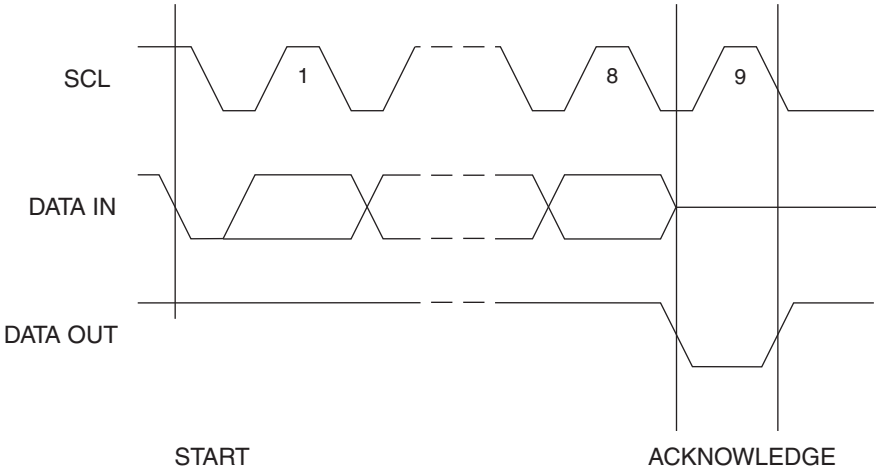


Figure 5-4. Output Acknowledge



6. Device Addressing

The 2K EEPROM device requires an 8-bit device address word following a start condition to enable the chip for a read or write operation (refer to Figure 8-1).

The device address word consists of a mandatory one, zero sequence for the first four most significant bits as shown. This is common to all the EEPROM devices.

The next 3 bits are the A2, A1 and A0 device address bits for the 2K EEPROM. These 3 bits must compare to their corresponding hard-wired input pins.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the chip will return to a standby state.

7. Write Operations

BYTE WRITE: A write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle, t_{WR}, to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see Figure 8-2 on page 11).

PAGE WRITE: The 2K EEPROM is capable of an 8-byte page write.

A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to seven data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see Figure 8-3 on page 11).

The data word address lower three bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than eight data words are transmitted to the EEPROM, the data word address will “roll over” and previous data will be overwritten.

ACKNOWLEDGE POLLING: Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero allowing the read or write sequence to continue.

8. Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to one. There are three read operations: current address read, random address read and sequential read.

CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page.

Once the device address with the read/write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition (see Figure 8-4 on page 11).

RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following stop condition (see Figure 8-5 on page 12).

SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a zero but does generate a following stop condition (see Figure 8-6 on page 12).

Figure 8-1. Device Address

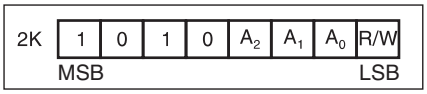


Figure 8-2. Byte Write

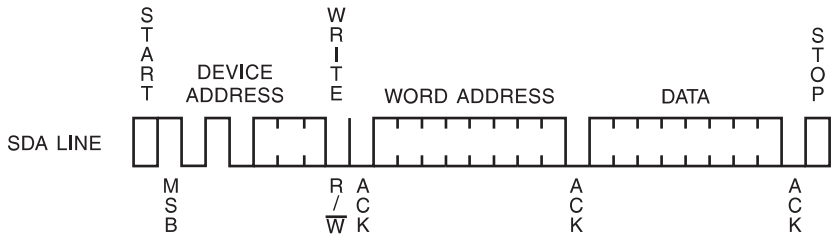


Figure 8-3. Page Write

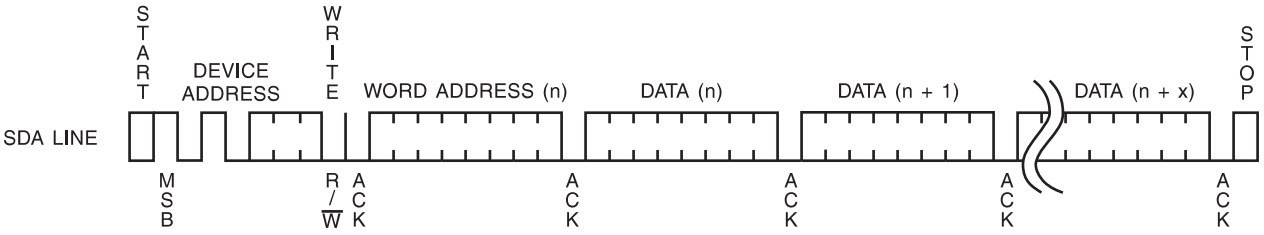


Figure 8-4. Current Address Read

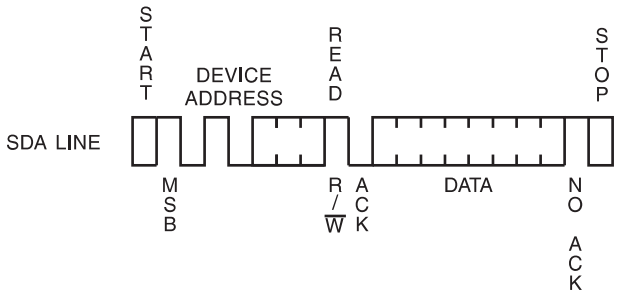


Figure 8-5. Random Read

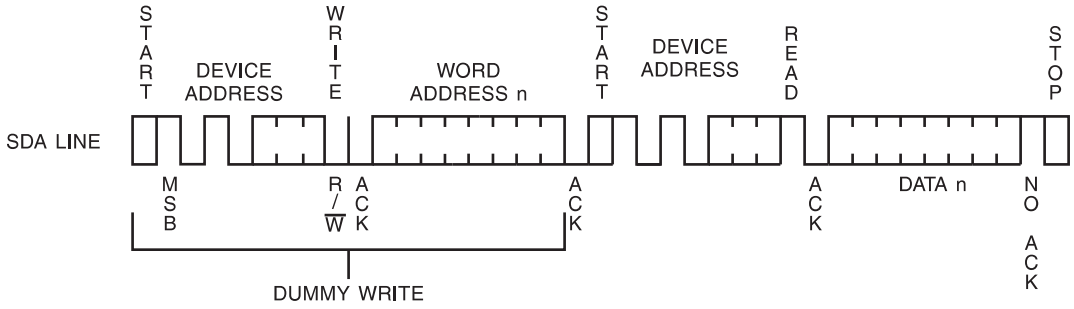
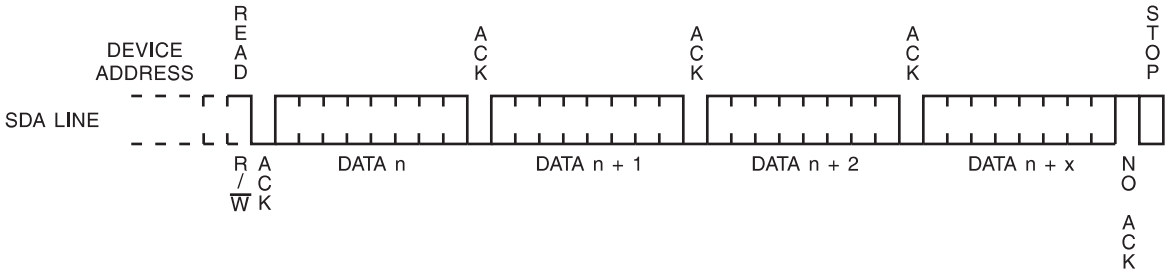
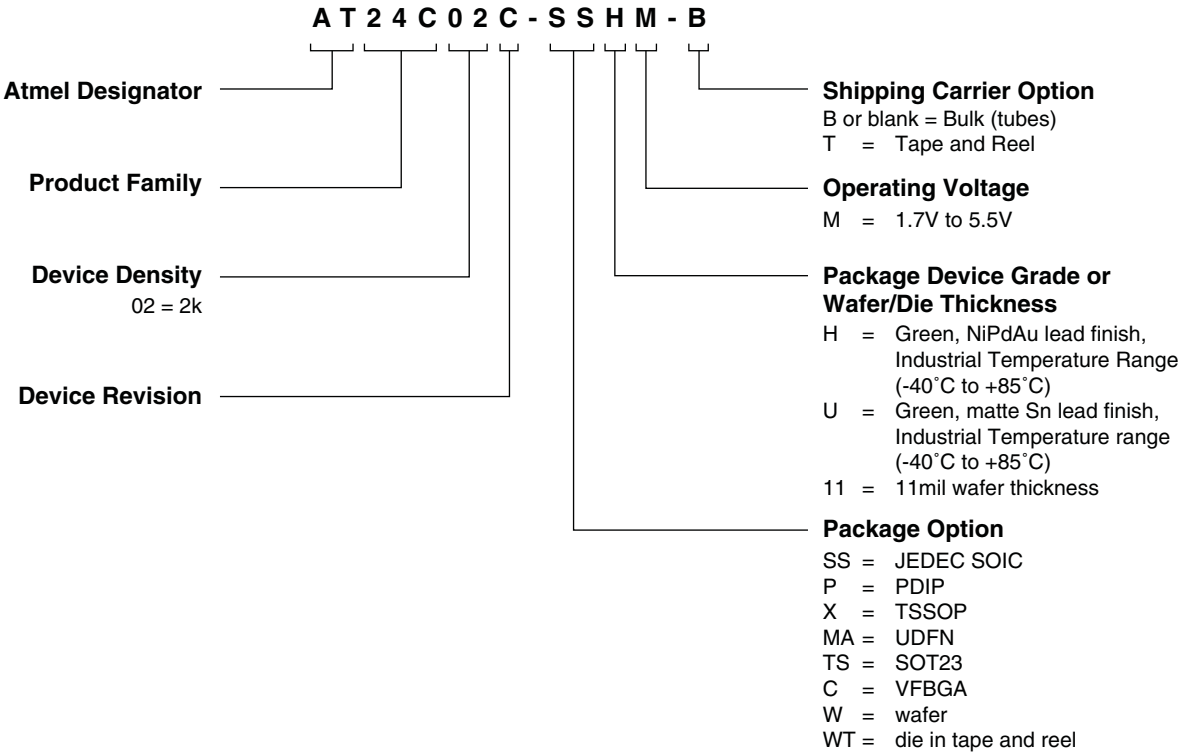


Figure 8-6. Sequential Read



9. AT24C02C Catalog Numbering Scheme



AT24C02C Ordering Information

Ordering Code	Voltage	Package	Operation Range
AT24C02C-PUM (Bulk form only)	1.7V to 5.5V	8P3	Lead-free/Halogen-free/ Industrial Temperature (–40°C to 85°C)
AT24C02C-SSHM-B[1] (NiPdAu Lead Finish)	1.7V to 5.5V	8S1	
AT24C02C-SSHM-T[2] (NiPdAu Lead Finish)	1.7V to 5.5V	8S1	
AT24C02C-XHM-T[2] (NiPdAu Lead Finish)	1.7V to 5.5V	8A2	
AT24C02C-XHM-B[1] (NiPdAu Lead Finish)	1.7V to 5.5V	8A2	
AT24C02CY6-MAHM-T[2] (NiPdAu Lead Finish)	1.7V to 5.5V	8Y6	
AT24C02C-TSUM-T[2]	1.7V to 5.5V	5TS1	
AT24C02CU3-CUM-T[2]	1.7V to 5.5V	8U3-1	
AT24C02C-W-11M[3]	1.7V to 5.5V	Die Sale	Industrial Temperature (–40°C to 85°C)

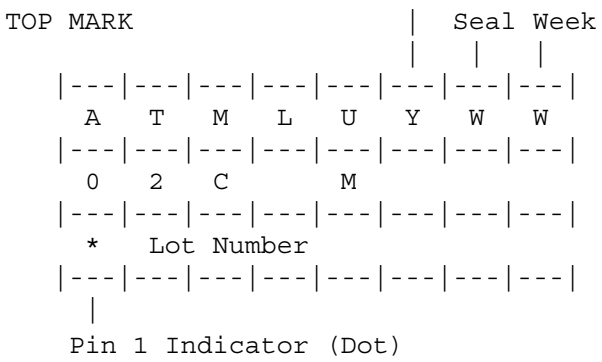
Notes: 1. "-B" denotes bulk.
2. "-T" denotes tape and reel. SOIC = 4K per reel. TSSOP, UDFN, SOT23, and VFBGA = 5K per reel.
3. Available in tape and reel and wafer form; order as SL788 for inkless wafer form. Please contact Serial Interface Marketing.

Package Type	
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
8A2	8-lead, 4.4 mm Body, Plastic Thin Shrink Small Outline Package (TSSOP)
8Y6	8-lead, 2.00 mm x 3.00 mm Body, 0.50 mm Pitch, Dual No Lead Package (UDFN)
5TS1	5-lead, 2.90 mm x 1.60 mm Body, Plastic Thin Shrink Small Outline Package (SOT23)
8U3-1	8-ball, die Ball Grid Array Package (VFBGA)

10. Part Marking Scheme

8-PDIP

Seal Year



U = Material Set

Y = Seal Year

WW = Seal Week

02C = Device

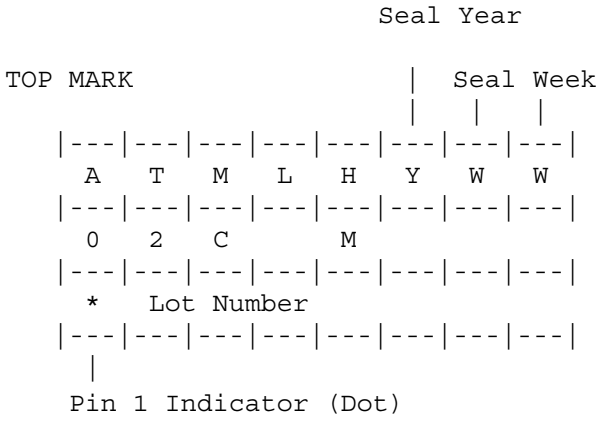
M = Voltage Indicator

*Lot Number to Use ALL Characters in Marking

BOTTOM MARK

No Bottom Mark

8-SOIC



H = Material Set

Y = Seal Year

WW = Seal Week

02C = Device

M = Voltage Indicator

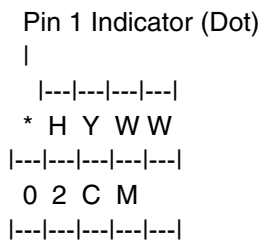
*Lot Number to Use ALL Characters in Marking

BOTTOM MARK

No Bottom Mark

8-TSSOP

TOP MARK



H = Material Set

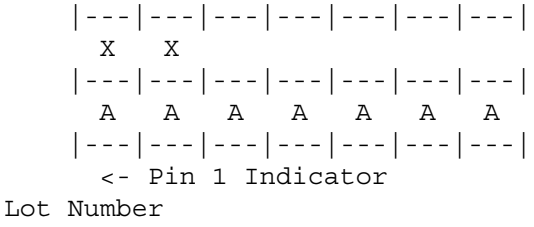
Y = Seal Year

WW = Seal Week

02C = Device

M = Voltage Indicator

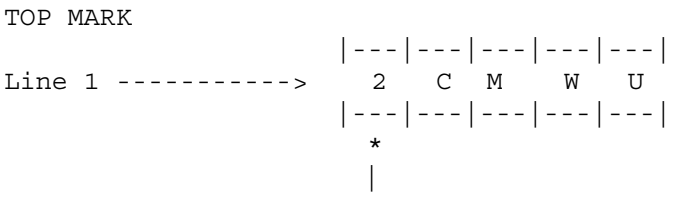
BOTTOM MARK



XX = Country of Origin

AAAAAA = Lot Number

SOT23



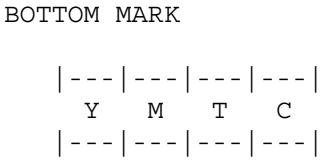
2C = Device

M = Voltage Indicator

W = Write Protect Feature

U = Material Set

Pin 1 Indicator (Dot)

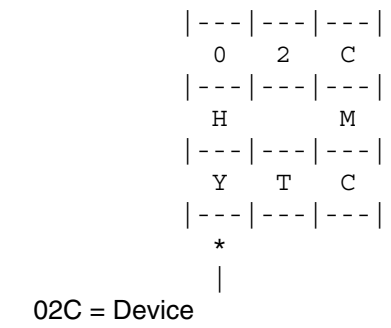


Y = One Digit Year Code

M = Seal Month

TC = Trace Code

UDFN



02C = Device

H = Material Set

M = Voltage Indicator

Y = Year of Assembly

TC = Trace Code

Pin 1 Indicator (Dot)

VFBGA

```
TOP MARK

LINE 1------->    02CU
LINE 2------->    YMTC
                  |<--  Pin 1 This Corner
```

02C = Device

U = Material Set

Y = One Digit Year Code

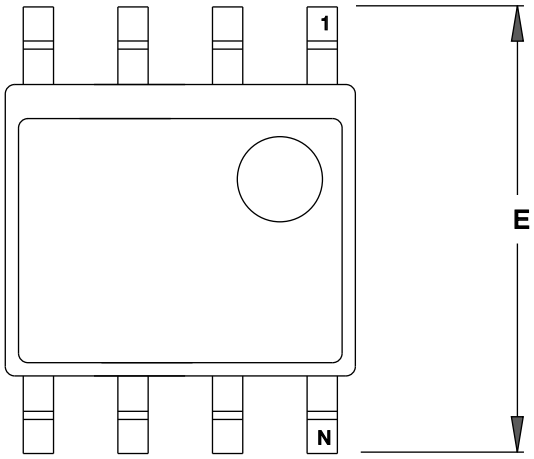
M = Seal Month

TC = Trace Code

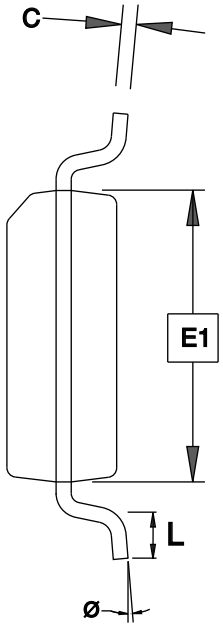
11. Packaging Information

8P3 – PDIP

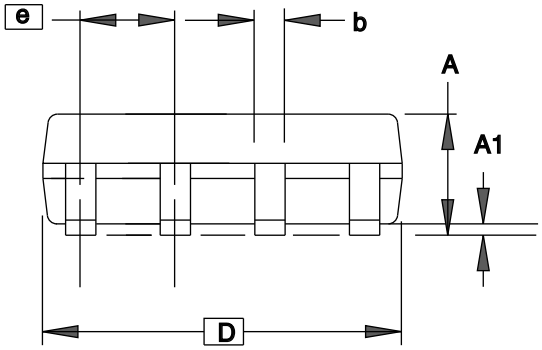
8S1 – JEDEC SOIC



TOP VIEW



END VIEW



SIDE VIEW

COMMON DIMENSIONS
(Unit of Measure = mm)

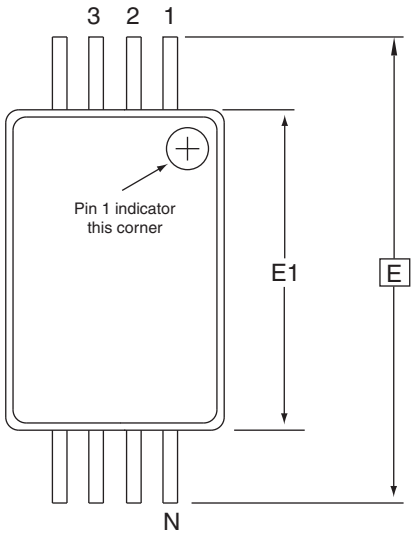
SYMBOL	MIN	NOM	MAX	NOTE
A	1.35	–	1.75	
A1	0.10	–	0.25	
b	0.31	–	0.51	
C	0.17	–	0.25	
D	4.80	–	5.05	
E1	3.81	–	3.99	
E	5.79	–	6.20	
e	1.27 BSC			
L	0.40	–	1.27	
θ	0°	–	8°	

Note: These drawings are for general information only. Refer to JEDEC Drawing MS-012, Variation AA for proper dimensions, tolerances, datums, etc.

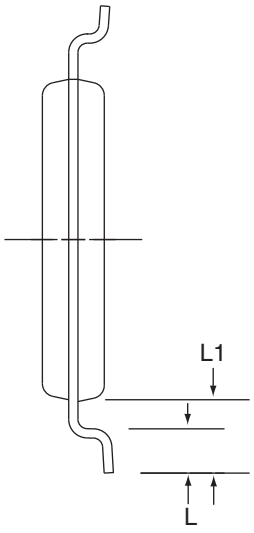
3/17/05

	TITLE	DRAWING NO.	REV.
1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906	**8S1**, 8-lead (0.150" Wide Body), Plastic Gull Wing Small Outline (JEDEC SOIC)	8S1	C

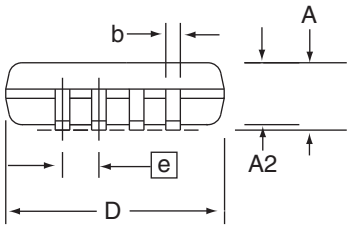
8A2 – TSSOP



Top View



End View



Side View

COMMON DIMENSIONS
(Unit of Measure = mm)

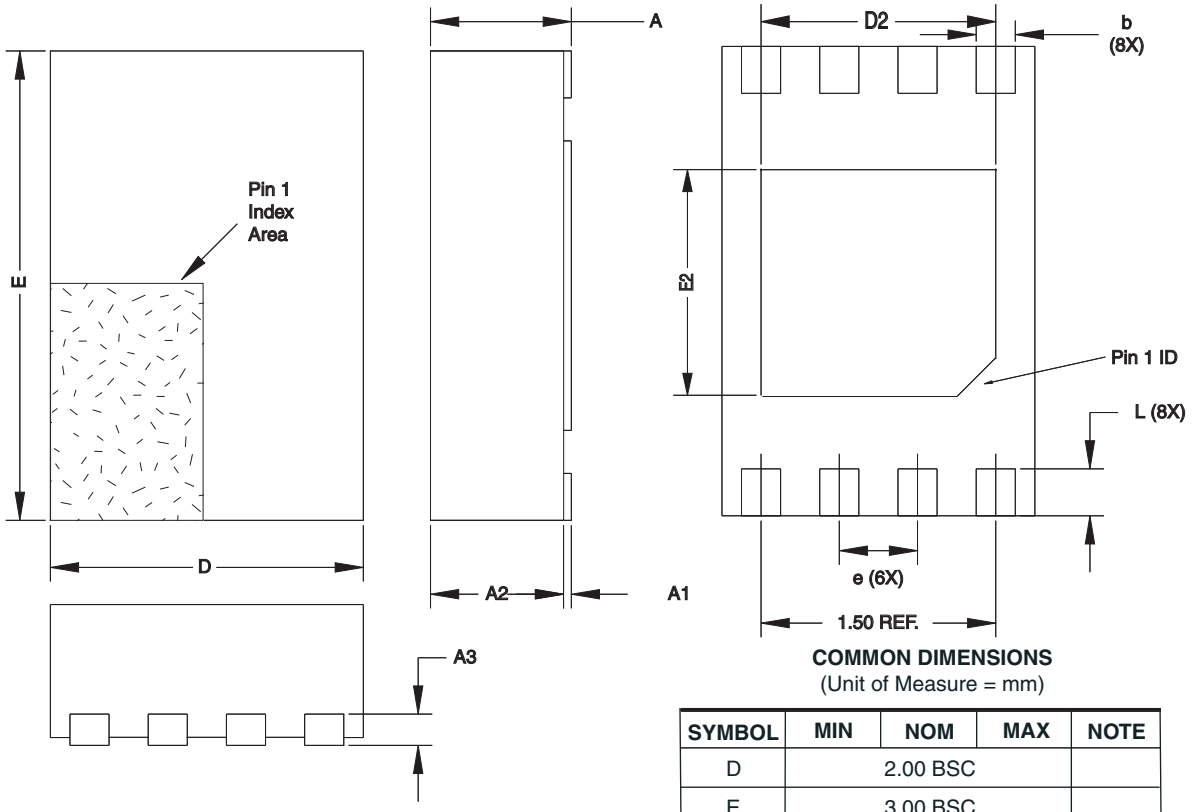
SYMBOL	MIN	NOM	MAX	NOTE
D	2.90	3.00	3.10	2, 5
E		6.40 BSC		
E1	4.30	4.40	4.50	3, 5
A	–	–	1.20	
A2	0.80	1.00	1.05	
b	0.19	–	0.30	4
e		0.65 BSC		
L	0.45	0.60	0.75	
L1		1.00 RE3		

Notes:
1. This drawing is for general information only. Refer to JEDEC Drawing MO-153, Variation AA, for proper dimensions, tolerances, datums, etc.
2. Dimension D does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
3. Dimension E1 does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010 in) per side.
4. Dimension b does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the b dimension at maximum material condition. Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and adjacent lead is 0.07 mm.
5. Dimension D and E1 to be determined at Datum Plane H.

10/29/08

	TITLE	GPC	DRAWING NO.	REV.
Package Drawing Contact: packagedrawings@atmel.com	**8A2,** 8-lead, 4.4mm Body, Plastic Thin Shrink Small Outline Package (TSSOP)	TNR	8A2	C

8Y6 - UDFN



COMMON DIMENSIONS
(Unit of Measure = mm)

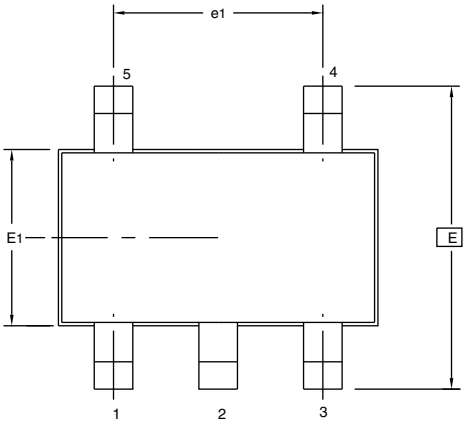
SYMBOL	MIN	NOM	MAX	NOTE
D		2.00 BSC		
E		3.00 BSC		
D2	1.40	1.50	1.60	
E2	-	-	1.40	
A	-	-	0.60	
A1	0.0	0.02	0.05	
A2	-	-	0.55	
A3		0.20 REF		
L	0.20	0.30	0.40	
e		0.50 BSC		
b	0.20	0.25	0.30	2

Notes:
1. This drawing is for general information only. Refer to JEDEC Drawing MO-229, for proper dimensions, tolerances, datums, etc.
2. Dimension b applies to metallized terminal and is measured between 0.15 mm and 0.30 mm from the terminal tip. If the terminal has the optional radius on the other end of the terminal, the dimension should not be measured in that radius area.
3. Soldering the large thermal pad is optional, but not recommended. No electrical connection is accomplished to the device through this pad, so if soldered it should be tied to ground

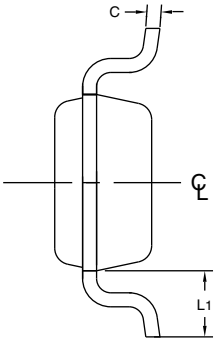
11/21/08

	TITLE	GPC	DRAWING NO.	REV.
Package Drawing Contact: packagedrawings@atmel.com	**8Y6, 8-lead** 2.0x3.0 mm Body, 0.50 mm Pitch, UltraThin Mini-MAP, Dual No Lead Package (Sawn)(UDFN)	YNZ	8Y6	E

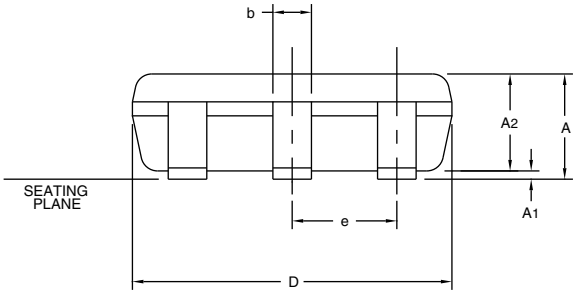
5TS1 – SOT23



TOP VIEW



END VIEW



SIDE VIEW

1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.15 mm per side.
2. The package top may be smaller than the package bottom. Dimensions D and E1 are determined at the outermost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
3. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.
4. Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall be 0.08 mm total in excess of the "b" dimension at maximum material condition. The dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and an adjacent lead shall not be less than 0.07 mm.

This drawing is for general information only. Refer to JEDEC Drawing MO-193, Variation AB for additional information.

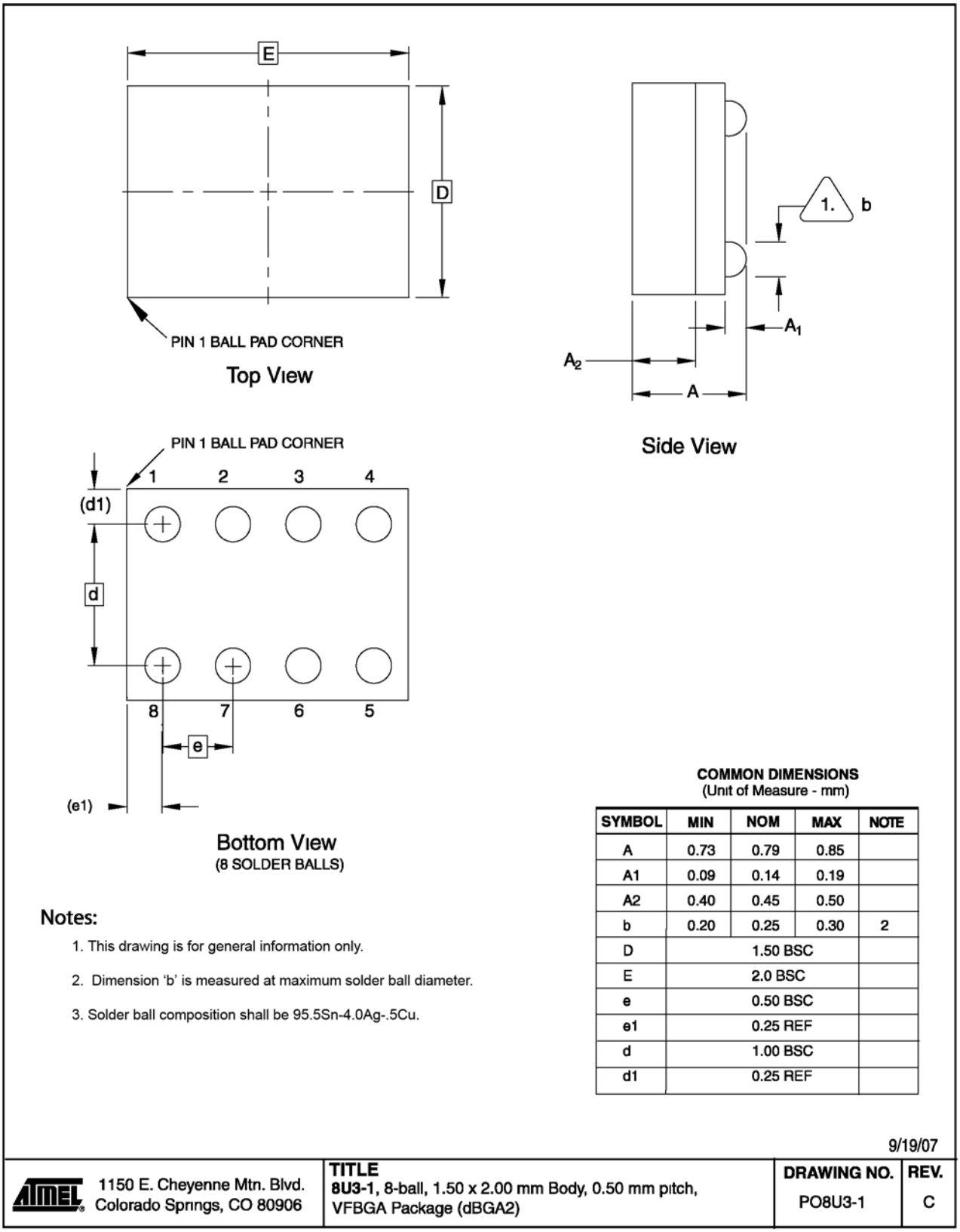
COMMON DIMENSIONS
(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	-	-	1.10	
A1	0.00	-	0.10	
A2	0.70	0.90	1.00	
c	0.08	-	0.20	3
D		2.90 BSC		1,2
E		2.80 BSC		1,2
E1		1.60 BSC		1,2
L1		0.60 REF		
e		0.95 BSC		
e1		1.90 BSC		
b	0.30	-	0.50	3,4

11/5/08

Package Drawing Contact: packagedrawings@atmel.com	TITLE 5TS1, 5-lead, 1.60 mm Body, Plastic Thin Shrink Small Outline Package (Shrink SOT)	GPC TSZ	DRAWING NO. 5TS1	REV. B

8U3-1 – VFBGA



COMMON DIMENSIONS
(Unit of Measure - mm)

SYMBOL	MIN	NOM	MAX	NOTE
A	0.73	0.79	0.85	
A1	0.09	0.14	0.19	
A2	0.40	0.45	0.50	
b	0.20	0.25	0.30	2
D	1.50 BSC			
E	2.0 BSC			
e	0.50 BSC			
e1	0.25 REF			
d	1.00 BSC			
d1	0.25 REF			

Notes:

1. This drawing is for general information only.
2. Dimension 'b' is measured at maximum solder ball diameter.
3. Solder ball composition shall be 95.5Sn-4.0Ag-.5Cu.

9/19/07

	TITLE	DRAWING NO.	REV.
1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906	**8U3-1**, 8-ball, 1.50 x 2.00 mm Body, 0.50 mm pitch, VFBGA Package (dBGA2)	PO8U3-1	C

12. Revision History

Doc. Rev.	Date	Comments
8700B	02/2010	Corrected Catalog Numbering Scheme and Ordering Information
8700A	12/2009	Initial Document Release

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